

**Amendments To The Claims:**

**Please amend the claims as follows:**

1. (*Currently amended*) A polishing composition used in a polishing process for reducing haze level of wafer surface, comprising:

hydroxyethyl cellulose compounded in said composition in a quantity larger than ~~0.01%~~ 0.05% by weight and smaller than ~~3%~~ 2% by weight and having an average molecular weight in the range of 300,000 to ~~3,000,000~~ 2,000,000;

polyethylene oxide compounded in said composition in a quantity larger than 0.005% by weight and smaller than 0.5% by weight and having an average molecular weight in the range of ~~30,000 to 50,000,000~~ 50,000 to 10,000,000;

~~an alkaline compound~~ ammonia compounded in said composition in a quantity larger than 0.02% by weight and smaller than 4% by weight;

water; and

silicon dioxide.

2. (*Original*) The polishing composition according to claim 1, wherein the total content of iron, nickel, copper, and calcium in the silicon dioxide, as measured in a 20 wt-% aqueous solution of said silicon dioxide, is 300 ppm or less.

3. (*Original*) The polishing composition according to claim 1, wherein the content of hydroxyethyl cellulose in the polishing composition is 0.1 to 1% by weight.

4. (*Original*) The polishing composition according to claim 1, wherein the content of silicon dioxide in the polishing composition is 3 to 20% by weight.

5. (*Canceled*)

6. (*New*) The polishing composition according to claim 1, wherein the content of hydroxyethyl cellulose in the polishing composition is 0.1 to 1% by weight.

**7. (New)** The polishing composition according to claim 1, wherein the average molecular weight of hydroxyethyl cellulose in the polishing composition is 600,000 to 2,000,000.

**8. (New)** The polishing composition according to claim 1, wherein the average molecular weight of hydroxyethyl cellulose in the polishing composition is 900,000 to 1,500,000.

**9. (New)** The polishing composition according to claim 1, wherein the content of polyethylene oxide in the polishing composition is 0.01 to 0.4% by weight.

**10. (New)** The polishing composition according to claim 1, wherein the content of polyethylene oxide in the polishing composition is 0.03 to 0.2% by weight.

**11. (New)** The polishing composition according to claim 1, wherein the average molecular weight of polyethylene oxide in the polishing composition is 100,000 to 1,000,000.

**12. (New)** The polishing composition according to claim 1, wherein the content of ammonia in the polishing composition is 0.03 to 3% by weight.

**13. (New)** The polishing composition according to claim 1, wherein the content of ammonia in the polishing composition is 0.2 to 2% by weight.